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Details

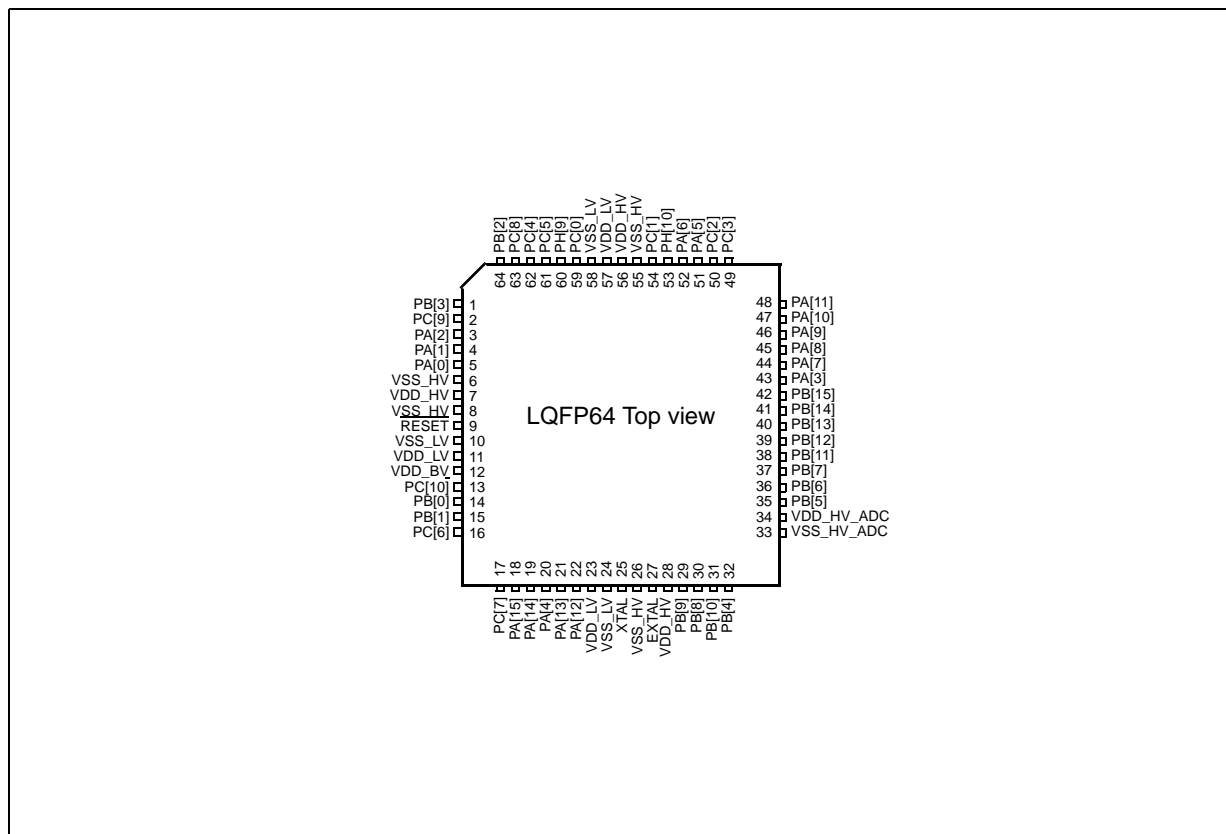
Product Status	Active
Core Processor	e200z0h
Core Size	32-Bit Single-Core
Speed	64MHz
Connectivity	CANbus, I ² C, LINbus, SCI, SPI
Peripherals	DMA, POR, PWM, WDT
Number of I/O	79
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	24K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 5.5V
Data Converters	A/D 28x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/spc560b40l3c4e0x

3 Package pinouts and signal descriptions

3.1 Package pinouts

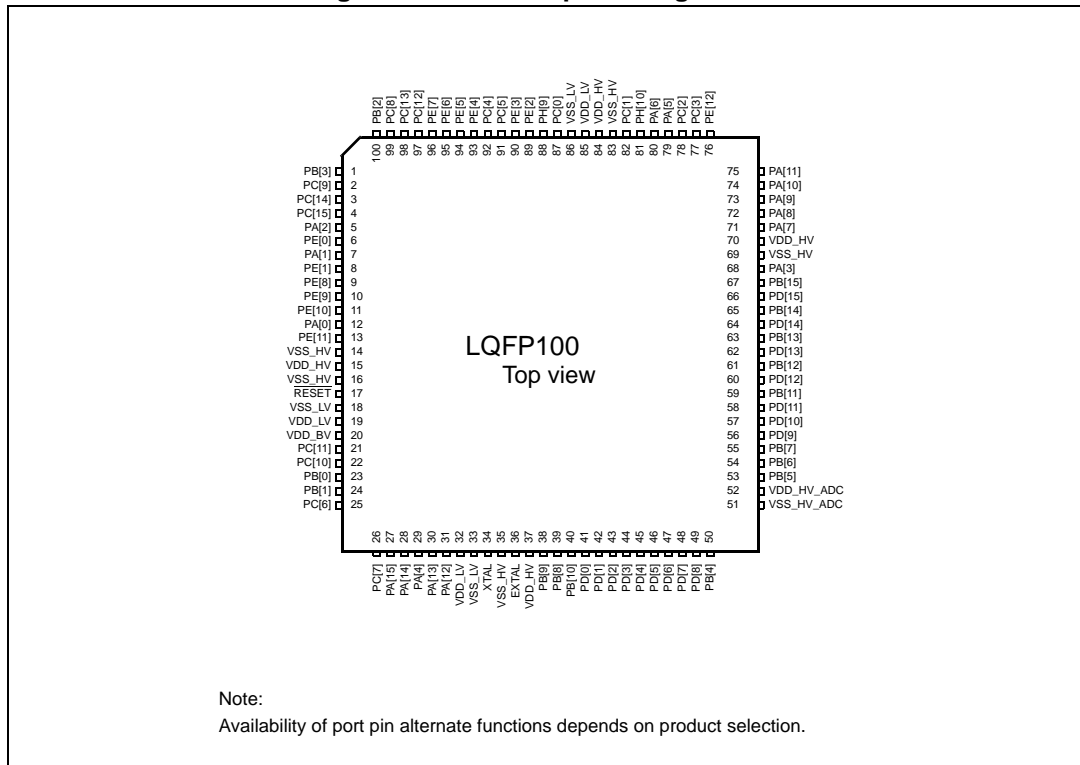
The available LQFP pinouts and the LPGA208 ballmap are provided in the following figures. For pin signal descriptions, please refer to the device reference manual (RM0017).

Figure 2. LQFP 64-pin configuration^(a)



a. All LQFP64 information is indicative and must be confirmed during silicon validation.

Figure 3. LQFP 100-pin configuration



3.5 System pins

The system pins are listed in [Table 5](#).

Table 5. System pin descriptions

System pin	Function	I/O direction	Pad type	RESET configuration	Pin number			
					LQFP64	LQFP100	LQFP144	LBGA208 ⁽¹⁾
RESET	Bidirectional reset with Schmitt-Trigger characteristics and noise filter.	I/O	M	Input, weak pull-up only after PHASE2	9	17	21	J1
EXTAL	Analog output of the oscillator amplifier circuit, when the oscillator is not in bypass mode. Analog input for the clock generator when the oscillator is in bypass mode. ⁽²⁾	I/O	X	Tristate	27	36	50	N8
XTAL	Analog input of the oscillator amplifier circuit. Needs to be grounded if oscillator is used in bypass mode. ⁽²⁾	I	X	Tristate	25	34	48	P8

1. LBGA208 available only as development package for Nexus2+

2. See the relevant section of the datasheet

3.6 Functional ports

The functional port pins are listed in [Table 6](#).

- c. All medium and fast pads are in slow configuration by default at reset and can be configured as fast or medium (see PCR.SRC in section Pad Configuration Registers (PCR0–PCR122) in the device reference manual).

Table 6. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function ⁽¹⁾	Function	Peripheral	I/O direction ⁽²⁾	Pad type	RESET configuration	Pin number			
								LQFP64	LQFP100	LQFP144	LBGA208 ⁽³⁾
PC[15]	PCR[47]	AF0 AF1 AF2 AF3	GPIO[47] E0UC[15] CS0_2 —	SIUL eMIOS_0 DSPI_2 —	I/O I/O I/O —	M	Tristate	—	4	4	D3
PD[0]	PCR[48]	AF0 AF1 AF2 AF3 —	GPIO[48] — — — GPI[4]	SIUL — — — ADC	I — — — I	I	Tristate	—	41	63	P12
PD[1]	PCR[49]	AF0 AF1 AF2 AF3 —	GPIO[49] — — — GPI[5]	SIUL — — — ADC	I — — — I	I	Tristate	—	42	64	T12
PD[2]	PCR[50]	AF0 AF1 AF2 AF3 —	GPIO[50] — — — GPI[6]	SIUL — — — ADC	I — — — I	I	Tristate	—	43	65	R12
PD[3]	PCR[51]	AF0 AF1 AF2 AF3 —	GPIO[51] — — — GPI[7]	SIUL — — — ADC	I — — — I	I	Tristate	—	44	66	P13
PD[4]	PCR[52]	AF0 AF1 AF2 AF3 —	GPIO[52] — — — GPI[8]	SIUL — — — ADC	I — — — I	I	Tristate	—	45	67	R13
PD[5]	PCR[53]	AF0 AF1 AF2 AF3 —	GPIO[53] — — — GPI[9]	SIUL — — — ADC	I — — — I	I	Tristate	—	46	68	T13

Table 6. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function ⁽¹⁾	Function	Peripheral	I/O direction ⁽²⁾	Pad type	RESET configuration	Pin number			
								LQFP64	LQFP100	LQFP144	LBGA208 ⁽³⁾
PD[6]	PCR[54]	AF0 AF1 AF2 AF3 —	GPIO[54] — — — GPI[10]	SIUL — — — ADC	I — — — I	I	Tristate	—	47	69	T14
PD[7]	PCR[55]	AF0 AF1 AF2 AF3 —	GPIO[55] — — — GPI[11]	SIUL — — — ADC	I — — — I	I	Tristate	—	48	70	R14
PD[8]	PCR[56]	AF0 AF1 AF2 AF3 —	GPIO[56] — — — GPI[12]	SIUL — — — ADC	I — — — I	I	Tristate	—	49	71	T15
PD[9]	PCR[57]	AF0 AF1 AF2 AF3 —	GPIO[57] — — — GPI[13]	SIUL — — — ADC	I — — — I	I	Tristate	—	56	78	N15
PD[10]	PCR[58]	AF0 AF1 AF2 AF3 —	GPIO[58] — — — GPI[14]	SIUL — — — ADC	I — — — I	I	Tristate	—	57	79	N14
PD[11]	PCR[59]	AF0 AF1 AF2 AF3 —	GPIO[59] — — — GPI[15]	SIUL — — — ADC	I — — — I	I	Tristate	—	58	80	N16
PD[12] ⁽⁸⁾	PCR[60]	AF0 AF1 AF2 AF3 —	GPIO[60] CS5_0 E0UC[24] — ANS[4]	SIUL DSPI_0 eMIOS_0 — ADC	I/O O I/O — I	J	Tristate	—	60	82	M15

11. Available only on SPC560Cx versions and SPC560B50B2 devices

12. Not available on SPC560B40L3 and SPC560B40L5 devices

13. Not available in 100 LQFP package

14. Available only on SPC560B50B2 devices

15. Not available on SPC560B44L3 devices

3.7 Nexus 2+ pins

In the LBGA208 package, eight additional debug pins are available (see [Table 7](#)).

Table 7. Nexus 2+ pin descriptions

Debug pin	Function	I/O direction	Pad type	Function after reset	Pin number		
					LQFP 100	LQFP 144	LBGA 208 ⁽¹⁾
MCKO	Message clock out	O	F	—	—	—	T4
MDO0	Message data out 0	O	M	—	—	—	H15
MDO1	Message data out 1	O	M	—	—	—	H16
MDO2	Message data out 2	O	M	—	—	—	H14
MDO3	Message data out 3	O	M	—	—	—	H13
EVTI	Event in	I	M	Pull-up	—	—	K1
EVTO	Event out	O	M	—	—	—	L4
MSEO	Message start/end out	O	M	—	—	—	G16

1. LBGA208 available only as development package for Nexus2+.

3.8 Electrical characteristics

3.9 Introduction

This section contains electrical characteristics of the device as well as temperature and power considerations.

This product contains devices to protect the inputs against damage due to high static voltages. However, it is advisable to take precautions to avoid applying any voltage higher than the specified maximum rated voltages.

To enhance reliability, unused inputs can be driven to an appropriate logic voltage level (V_{DD} or V_{SS}). This could be done by the internal pull-up and pull-down, which is provided by the product for most general purpose pins.

The parameters listed in the following tables represent the characteristics of the device and its demands on the system.

In the tables where the device logic provides signals with their respective timing characteristics, the symbol “CC” for Controller Characteristics is included in the Symbol column.

Table 14. Recommended operating conditions (5.0 V) (continued)

Symbol		Parameter	Conditions	Value		Unit
				Min	Max	
I_{INJPAD}	SR	Injected input current on any pin during overload condition	—	–5	5	mA
I_{INJSUM}	SR	Absolute sum of all injected input currents during overload condition	—	–50	50	
TV_{DD}	SR	V_{DD} slope to ensure correct power up ⁽⁶⁾	—	3.0 ⁽⁷⁾	250×10^3 (0.25 [V/μs])	V/s

- 100 nF capacitance needs to be provided between each V_{DD}/V_{SS} pair.
- Full device operation is guaranteed by design when the voltage drops below 4.5 V down to 3.0 V. However, certain analog electrical characteristics will not be guaranteed to stay within the stated limits.
- 330 nF capacitance needs to be provided between each V_{DD_LV}/V_{SS_LV} supply pair.
- 100 nF capacitance needs to be provided between V_{DD_BV} and the nearest V_{SS_LV} (higher value may be needed depending on external regulator characteristics).
- 1 μF (electrolytic/tantalum) + 47 nF (ceramic) capacitance needs to be provided between V_{DD_ADC}/V_{SS_ADC} pair. Another ceramic cap of 10 nF with low inductance package can be added.
- Guaranteed by device validation.
- Minimum value of TV_{DD} must be guaranteed until V_{DD} reaches 2.6 V (maximum value of V_{PORH}).

Note: RAM data retention is guaranteed with V_{DD_LV} not below 1.08 V.

3.14 Thermal characteristics

3.14.1 Package thermal characteristics

Table 15. LQFP thermal characteristics⁽¹⁾

Symbol		C	Parameter	Conditions ⁽²⁾	Pin count	Value	Unit
$R_{\theta JA}$	CC	D	Thermal resistance, junction-to-ambient natural convection ⁽³⁾	Single-layer board - 1s	64	60	°C/W
					100	64	
					144	64	
				Four-layer board - 2s2p	64	42	
					100	51	
					144	49	
$R_{\theta JB}$	CC	D	Thermal resistance, junction-to-board ⁽⁴⁾	Single-layer board - 1s	64	24	°C/W
					100	36	
					144	37	
				Four-layer board - 2s2p	64	24	
					100	34	
					144	35	

Table 18. SLOW configuration output buffer electrical characteristics (continued)

Symbol	C	Parameter	Conditions ⁽¹⁾	Value			Unit
				Min	Typ	Max	
V _{OL}	CC	Output low level SLOW configuration	Push Pull	I _{OL} = 2 mA, V _{DD} = 5.0 V ± 10%, PAD3V5V = 0 (recommended)	—	—	0.1V _{DD}
				I _{OL} = 2 mA, V _{DD} = 5.0 V ± 10%, PAD3V5V = 1 ⁽²⁾	—	—	0.1V _{DD}
				I _{OL} = 1 mA, V _{DD} = 3.3 V ± 10%, PAD3V5V = 1 (recommended)	—	—	0.5

1. V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = -40 to 125 °C, unless otherwise specified

2. The configuration PAD3V5 = 1 when V_{DD} = 5 V is only a transient configuration during power-up. All pads but RESET and Nexus output (MDOx, EVTO, MCKO) are configured in input or in high impedance state.

Table 19. MEDIUM configuration output buffer electrical characteristics

Symbol	C	Parameter	Conditions ⁽¹⁾	Value			Unit
				Min	Typ	Max	
V _{OH}	CC	Output high level MEDIUM configuration	Push Pull	I _{OH} = -3.8 mA, V _{DD} = 5.0 V ± 10%, PAD3V5V = 0	0.8V _{DD}	—	V
				I _{OH} = -2 mA, V _{DD} = 5.0 V ± 10%, PAD3V5V = 0 (recommended)	0.8V _{DD}	—	
				I _{OH} = -1 mA, V _{DD} = 5.0 V ± 10%, PAD3V5V = 1 ⁽²⁾	0.8V _{DD}	—	
				I _{OH} = -1 mA, V _{DD} = 3.3 V ± 10%, PAD3V5V = 1 (recommended)	V _{DD} -0.8	—	
				I _{OH} = -100 µA, V _{DD} = 5.0 V ± 10%, PAD3V5V = 0	0.8V _{DD}	—	
V _{OL}	CC	Output low level MEDIUM configuration	Push Pull	I _{OL} = 3.8 mA, V _{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	V
				I _{OL} = 2 mA, V _{DD} = 5.0 V ± 10%, PAD3V5V = 0 (recommended)	—	—	
				I _{OL} = 1 mA, V _{DD} = 5.0 V ± 10%, PAD3V5V = 1 ⁽²⁾	—	—	
				I _{OL} = 1 mA, V _{DD} = 3.3 V ± 10%, PAD3V5V = 1 (recommended)	—	—	
				I _{OL} = 100 µA, V _{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	

1. V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = -40 to 125 °C, unless otherwise specified

Table 23. I/O consumption

Symbol		C	Parameter	Conditions ⁽¹⁾		Value			Unit
						Min	Typ	Max	
$I_{\text{SWTSLW}}^{(2)}$	CC	D	Dynamic I/O current for SLOW configuration	$C_L = 25 \text{ pF}$	$V_{\text{DD}} = 5.0 \text{ V} \pm 10\%$, $\text{PAD3V5V} = 0$	—	—	20	mA
					$V_{\text{DD}} = 3.3 \text{ V} \pm 10\%$, $\text{PAD3V5V} = 1$	—	—	16	
$I_{\text{SWTMED}}^{(2)}$	CC	D	Dynamic I/O current for MEDIUM configuration	$C_L = 25 \text{ pF}$	$V_{\text{DD}} = 5.0 \text{ V} \pm 10\%$, $\text{PAD3V5V} = 0$	—	—	29	mA
					$V_{\text{DD}} = 3.3 \text{ V} \pm 10\%$, $\text{PAD3V5V} = 1$	—	—	17	
$I_{\text{SWTFST}}^{(2)}$	CC	D	Dynamic I/O current for FAST configuration	$C_L = 25 \text{ pF}$	$V_{\text{DD}} = 5.0 \text{ V} \pm 10\%$, $\text{PAD3V5V} = 0$	—	—	110	mA
					$V_{\text{DD}} = 3.3 \text{ V} \pm 10\%$, $\text{PAD3V5V} = 1$	—	—	50	
I_{RMSSLW}	CC	D	Root mean square I/O current for SLOW configuration	$C_L = 25 \text{ pF}, 2 \text{ MHz}$	$V_{\text{DD}} = 5.0 \text{ V} \pm 10\%$, $\text{PAD3V5V} = 0$	—	—	2.3	mA
				$C_L = 25 \text{ pF}, 4 \text{ MHz}$		—	—	3.2	
				$C_L = 100 \text{ pF}, 2 \text{ MHz}$		—	—	6.6	
				$C_L = 25 \text{ pF}, 2 \text{ MHz}$	$V_{\text{DD}} = 3.3 \text{ V} \pm 10\%$, $\text{PAD3V5V} = 1$	—	—	1.6	
				$C_L = 25 \text{ pF}, 4 \text{ MHz}$		—	—	2.3	
				$C_L = 100 \text{ pF}, 2 \text{ MHz}$		—	—	4.7	
I_{RMSMED}	CC	D	Root mean square I/O current for MEDIUM configuration	$C_L = 25 \text{ pF}, 13 \text{ MHz}$	$V_{\text{DD}} = 5.0 \text{ V} \pm 10\%$, $\text{PAD3V5V} = 0$	—	—	6.6	mA
				$C_L = 25 \text{ pF}, 40 \text{ MHz}$		—	—	13.4	
				$C_L = 100 \text{ pF}, 13 \text{ MHz}$		—	—	18.3	
				$C_L = 25 \text{ pF}, 13 \text{ MHz}$	$V_{\text{DD}} = 3.3 \text{ V} \pm 10\%$, $\text{PAD3V5V} = 1$	—	—	5	
				$C_L = 25 \text{ pF}, 40 \text{ MHz}$		—	—	8.5	
				$C_L = 100 \text{ pF}, 13 \text{ MHz}$		—	—	11	
I_{RMSFST}	CC	D	Root mean square I/O current for FAST configuration	$C_L = 25 \text{ pF}, 40 \text{ MHz}$	$V_{\text{DD}} = 5.0 \text{ V} \pm 10\%$, $\text{PAD3V5V} = 0$	—	—	22	mA
				$C_L = 25 \text{ pF}, 64 \text{ MHz}$		—	—	33	
				$C_L = 100 \text{ pF}, 40 \text{ MHz}$		—	—	56	
				$C_L = 25 \text{ pF}, 40 \text{ MHz}$	$V_{\text{DD}} = 3.3 \text{ V} \pm 10\%$, $\text{PAD3V5V} = 1$	—	—	14	
				$C_L = 25 \text{ pF}, 64 \text{ MHz}$		—	—	20	
				$C_L = 100 \text{ pF}, 40 \text{ MHz}$		—	—	35	
I_{AVGSEG}	SR	D	Sum of all the static I/O current within a supply segment	$V_{\text{DD}} = 5.0 \text{ V} \pm 10\%$, $\text{PAD3V5V} = 0$	—	—	70	mA	
				$V_{\text{DD}} = 3.3 \text{ V} \pm 10\%$, $\text{PAD3V5V} = 1$	—	—	65		

1. $V_{\text{DD}} = 3.3 \text{ V} \pm 10\% / 5.0 \text{ V} \pm 10\%$, $T_A = -40$ to 125°C , unless otherwise specified

2. Stated maximum values represent peak consumption that lasts only a few ns during I/O transition.

[Table 24](#) provides the weight of concurrent switching I/Os.

Table 24. I/O weight⁽¹⁾ (continued)

Supply segment			Pad	LQFP144/LQFP100				LQFP64 ⁽²⁾			
				Weight 5 V		Weight 3.3 V		Weight 5 V		Weight 3.3 V	
LQFP 144	LQFP 100	LQFP 64		SRC ⁽³⁾ = 0	SRC = 1	SRC = 0	SRC = 1	SRC = 0	SRC = 1	SRC = 0	SRC = 1
1	—	—	PG[9]	9%	—	10%	—	—	—	—	—
	—	—	PG[8]	9%	—	11%	—	—	—	—	—
	1	—	PC[11]	9%	—	11%	—	—	—	—	—
		1	PC[10]	9%	13%	11%	12%	9%	13%	11%	12%
	—	—	PG[7]	10%	14%	11%	12%	—	—	—	—
	—	—	PG[6]	10%	14%	12%	12%	—	—	—	—
	1	1	PB[0]	10%	14%	12%	12%	10%	14%	12%	12%
			PB[1]	10%	—	12%	—	10%	—	12%	—
	—	—	PF[9]	10%	—	12%	—	—	—	—	—
	—	—	PF[8]	10%	15%	12%	13%	—	—	—	—
	—	—	PF[12]	10%	15%	12%	13%	—	—	—	—
	1	1	PC[6]	10%	—	12%	—	10%	—	12%	—
			PC[7]	10%	—	12%	—	10%	—	12%	—
	—	—	PF[10]	10%	14%	12%	12%	—	—	—	—
	—	—	PF[11]	10%	—	11%	—	—	—	—	—
	1	1	PA[15]	9%	12%	10%	11%	9%	12%	10%	11%
	—	—	PF[13]	8%	—	10%	—	—	—	—	—
	1	1	PA[14]	8%	11%	9%	10%	8%	11%	9%	10%
			PA[4]	8%	—	9%	—	8%	—	9%	—
			PA[13]	7%	10%	9%	9%	7%	10%	9%	9%
			PA[12]	7%	—	8%	—	7%	—	8%	—

Table 24. I/O weight⁽¹⁾ (continued)

Supply segment			Pad	LQFP144/LQFP100				LQFP64 ⁽²⁾			
				Weight 5 V		Weight 3.3 V		Weight 5 V		Weight 3.3 V	
LQFP 144	LQFP 100	LQFP 64		SRC ⁽³⁾ = 0	SRC = 1	SRC = 0	SRC = 1	SRC = 0	SRC = 1	SRC = 0	SRC = 1
3	3	2	PA[5]	5%	7%	6%	6%	6%	8%	7%	7%
			PA[6]	5%	—	6%	—	5%	—	6%	—
			PH[10]	4%	6%	5%	5%	5%	7%	6%	6%
			PC[1]	5%	—	5%	—	5%	—	5%	—
4	4	3	PC[0]	6%	9%	7%	8%	6%	9%	7%	8%
			PH[9]	7	7	8	8	7	7	8	8
		—	PE[2]	7%	10%	9%	9%	—	—	—	—
		—	PE[3]	8%	11%	9%	9%	—	—	—	—
		3	PC[5]	8%	11%	9%	10%	8%	11%	9%	10%
			PC[4]	8%	12%	10%	10%	8%	12%	10%	10%
		—	PE[4]	8%	12%	10%	11%	—	—	—	—
		—	PE[5]	9%	12%	10%	11%	—	—	—	—
	—	—	PH[4]	9%	13%	11%	11%	—	—	—	—
	—	—	PH[5]	9%	—	11%	—	—	—	—	—
	—	—	PH[6]	9%	13%	11%	12%	—	—	—	—
	—	—	PH[7]	9%	13%	11%	12%	—	—	—	—
	—	—	PH[8]	10%	14%	11%	12%	—	—	—	—
	4	—	PE[6]	10%	14%	12%	12%	—	—	—	—
		—	PE[7]	10%	14%	12%	12%	—	—	—	—
		—	PC[12]	10%	14%	12%	13%	—	—	—	—
		—	PC[13]	10%	—	12%	—	—	—	—	—
		3	PC[8]	10%	—	12%	—	10%	—	12%	—
			PB[2]	10%	15%	12%	13%	10%	15%	12%	13%

1. $V_{DD} = 3.3\text{ V} \pm 10\% / 5.0\text{ V} \pm 10\%$, $T_A = -40$ to $125\text{ }^{\circ}\text{C}$, unless otherwise specified

2. All LQFP64 information is indicative and must be confirmed during silicon validation.

3. SRC: "Slew Rate Control" bit in SIU_PCR

3.16 RESET electrical characteristics

The device implements a dedicated bidirectional $\overline{\text{RESET}}$ pin.

Figure 7. Start-up reset requirements

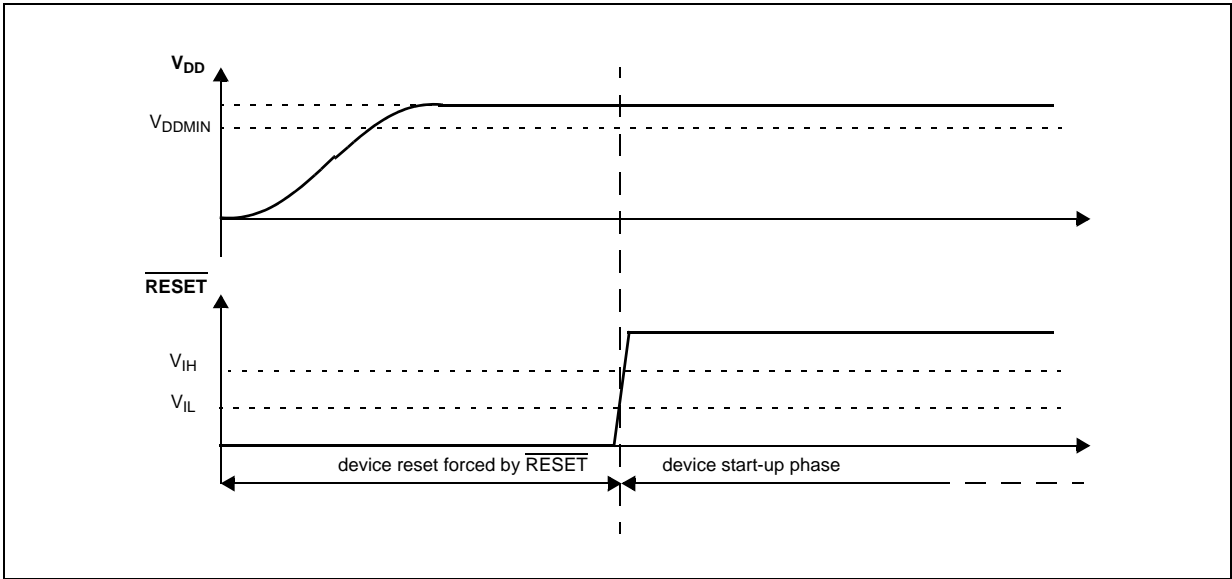


Figure 8. Noise filtering on reset signal

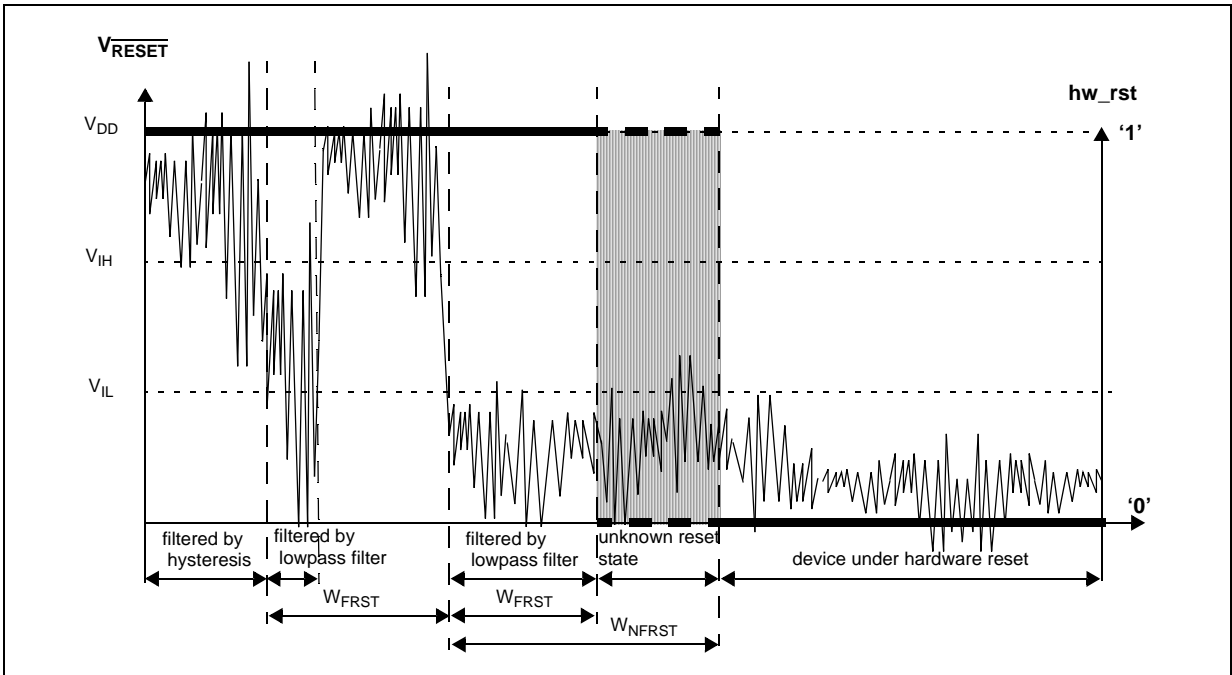
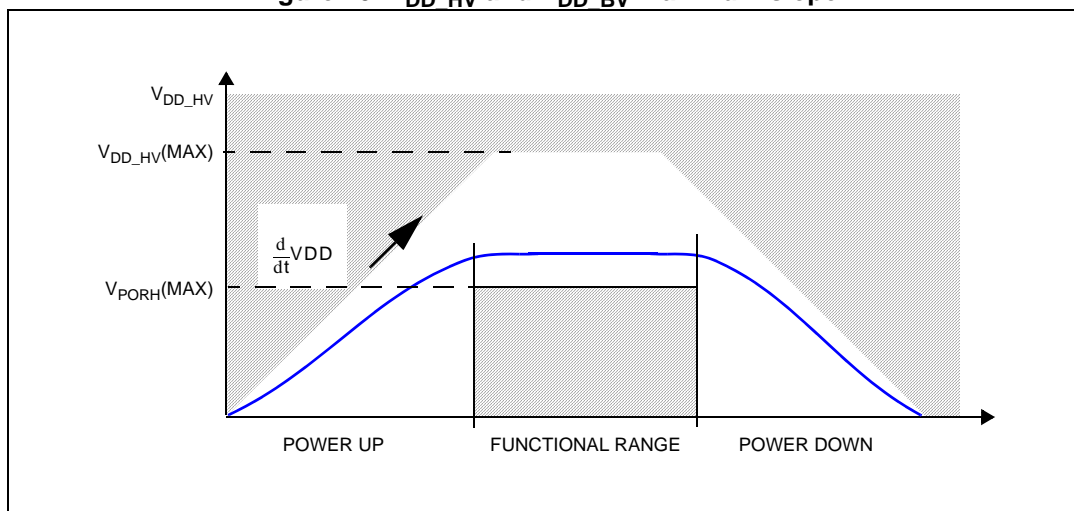


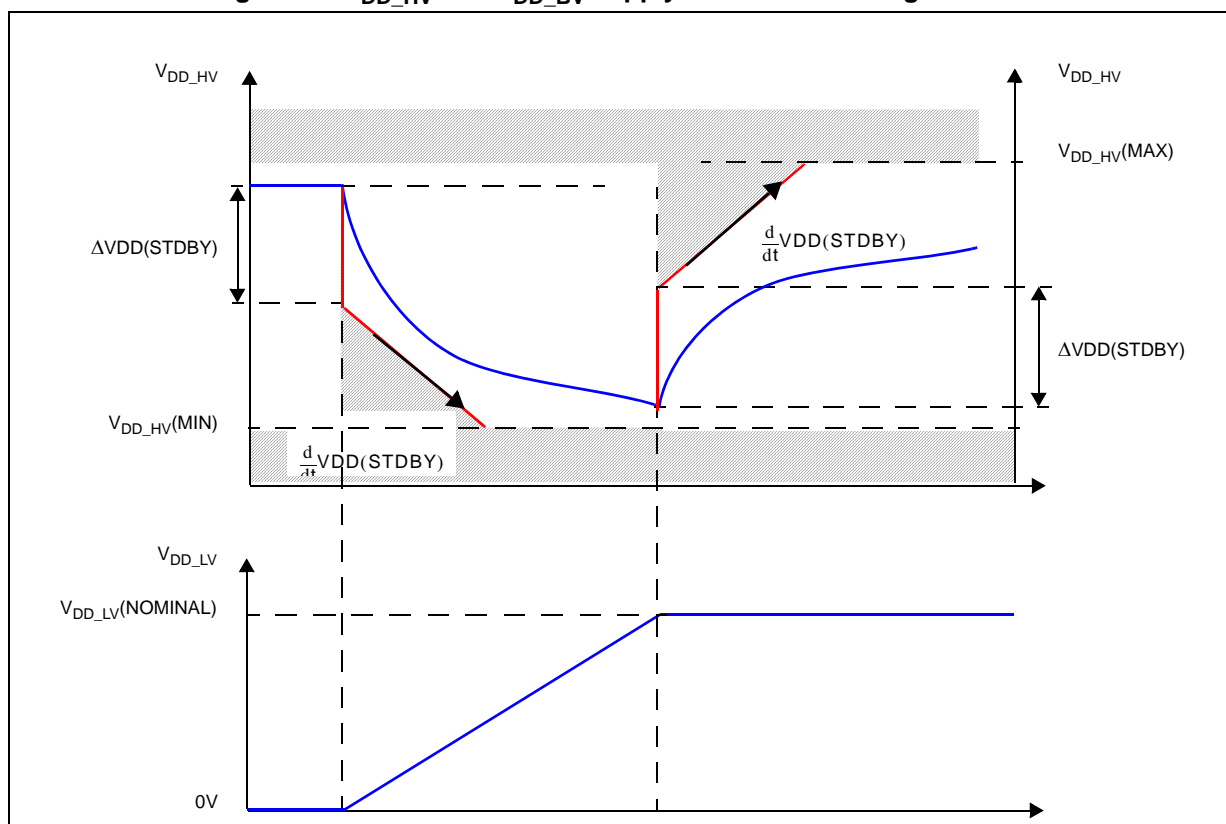
Table 25. Reset electrical characteristics

Symbol	C	Parameter	Conditions ⁽¹⁾	Value			Unit
				Min	Typ	Max	
V_{IH}	SR	P	Input High Level CMOS (Schmitt Trigger)	$0.65V_{DD}$	—	$V_{DD}+0.4$	V
V_{IL}	SR	P	Input low Level CMOS (Schmitt Trigger)	-0.4	—	$0.35V_{DD}$	V

Figure 10. V_{DD_HV} and V_{DD_BV} maximum slope

When STANDBY mode is used, further constraints are applied to the both V_{DD_HV} and V_{DD_BV} in order to guarantee correct regulator function during STANDBY exit. This is described on [Figure 11](#).

STANDBY regulator constraints should normally be guaranteed by implementing equivalent of CSTDBY capacitance on application board (capacitance and ESR typical values), but would actually depend on exact characteristics of application external regulator.

Figure 11. V_{DD_HV} and V_{DD_BV} supply constraints during STANDBY mode exit

released as soon as internal reset sequence is completed regardless of LVDHV5H threshold.

Table 27. Low voltage detector electrical characteristics

Symbol		C	Parameter	Conditions ⁽¹⁾	Value			Unit
					Min	Typ	Max	
V _{PORUP}	SR	P	Supply for functional POR module	—	1.0	—	5.5	V
V _{PORH}	CC	P	Power-on reset threshold	T _A = 25 °C, after trimming	1.5	—	2.6	
		T		—	1.5	—	2.6	
V _{LVDHV3H}	CC	T	LVDHV3 low voltage detector high threshold	—	—	—	2.95	
V _{LVDHV3L}	CC	P	LVDHV3 low voltage detector low threshold		2.6	—	2.9	
V _{LVDHV5H}	CC	T	LVDHV5 low voltage detector high threshold		—	—	4.5	
V _{LVDHV5L}	CC	P	LVDHV5 low voltage detector low threshold		3.8	—	4.4	
V _{LVDLVCORL}	CC	P	LVDLVCOR low voltage detector low threshold		1.08	—	1.16	
V _{LVDLVBKPL}	CC	P	LVDLVBKP low voltage detector low threshold		1.08	—	1.16	

1. V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = -40 to 125 °C, unless otherwise specified

3.18 Power consumption

Table 28 provides DC electrical characteristics for significant application modes. These values are indicative values; actual consumption depends on the application.

Table 28. Power consumption on VDD_BV and VDD_HV

Symbol		C	Parameter	Conditions ⁽¹⁾	Value			Unit	
					Min	Typ	Max		
I _{DDMAX} ⁽²⁾	CC	D	RUN mode maximum average current	—		—	115	140 ⁽³⁾	mA
I _{DDRUN} ⁽⁴⁾	CC	T	RUN mode typical average current ⁽⁵⁾	f _{CPU} = 8 MHz		—	7	—	mA
		f _{CPU} = 16 MHz		—	18	—			
		f _{CPU} = 32 MHz		—	29	—			
		f _{CPU} = 48 MHz		—	40	100			
		f _{CPU} = 64 MHz		—	51	125			
I _{DDHALT}	CC	C	HALT mode current ⁽⁶⁾	Slow internal RC oscillator (128 kHz) running	T _A = 25 °C	—	8	15	mA
		P			T _A = 125 °C	—	14	25	

3.19.3 Start-up/Switch-off timings

Table 33. Start-up time/Switch-off time

Symbol	C		Parameter	Conditions ⁽¹⁾	Value			Unit
					Min	Typ	Max	
T _{FLARSTEXIT}	CC	T	Delay for Flash module to exit reset mode	Code Flash	—	—	125	μs
		T		Data Flash	—	—	125	
T _{FLALPEXIT}	CC	T	Delay for Flash module to exit low-power mode	Code Flash	—	—	0.5	
		T		Data Flash	—	—	0.5	
T _{FLAPDEXIT}	CC	T	Delay for Flash module to exit power-down mode	Code Flash	—	—	30	
		T		Data Flash	—	—	30	
T _{FLALPENTRY}	CC	T	Delay for Flash module to enter low-power mode	Code Flash	—	—	0.5	
		T		Data Flash	—	—	0.5	
T _{FLAPDENTRY}	CC	T	Delay for Flash module to enter power-down mode	Code Flash	—	—	1.5	
		T		Data Flash	—	—	1.5	

1. V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = -40 to 125 °C, unless otherwise specified

3.20 Electromagnetic compatibility (EMC) characteristics

Susceptibility tests are performed on a sample basis during product characterization.

3.20.1 Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user apply EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

- Software recommendations: The software flowchart must include the management of runaway conditions such as:
 - Corrupted program counter
 - Unexpected reset
 - Critical data corruption (control registers...)
- Prequalification trials: Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the reset pin or the oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note *Software Techniques For Improving Microcontroller EMC Performance* (AN1015)).

Figure 13. Crystal oscillator and resonator connection scheme

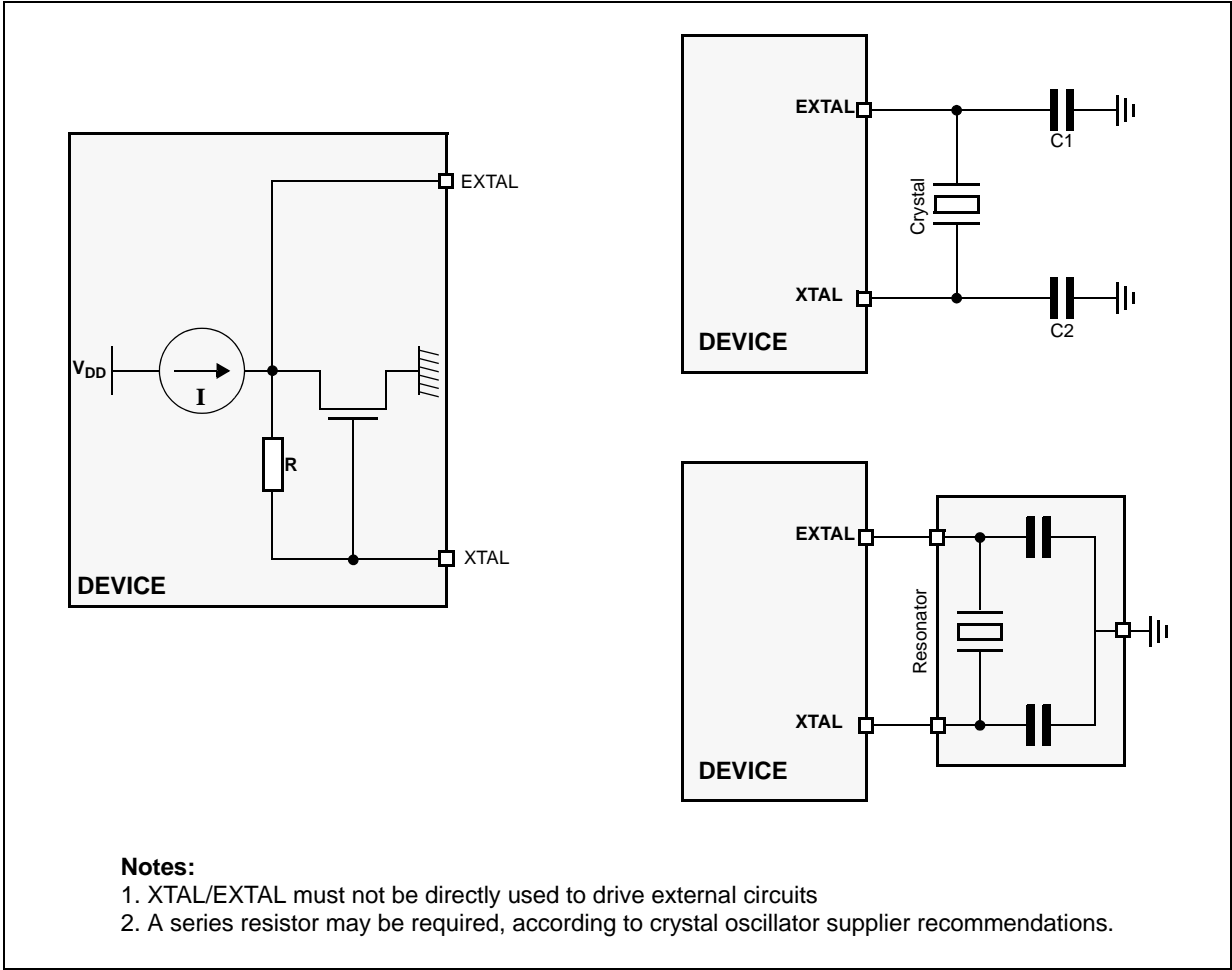


Table 37. Crystal description

Nominal frequency (MHz)	NDK crystal reference	Crystal equivalent series resistance ESR Ω	Crystal motional capacitance (C_m) fF	Crystal motional inductance (L_m) mH	Load on xtalin/xtalout $C1 = C2$ (pF) ⁽¹⁾	Shunt capacitance between xtalout and xtalin $C0$ ⁽²⁾ (pF)
4	NX8045GB	300	2.68	591.0	21	2.93
8	NX5032GA	300	2.46	160.7	17	3.01
10		150	2.93	86.6	15	2.91
12		120	3.11	56.5	15	2.93
16		120	3.90	25.3	10	3.00

1. The values specified for C1 and C2 are the same as used in simulations. It should be ensured that the testing includes all the parasitics (from the board, probe, crystal, etc.) as the AC / transient behavior depends upon them.
2. The value of C0 specified here includes 2 pF additional capacitance for parasitics (to be seen with bond-pads, package, etc.).

3.27.2 DSPI characteristics

Table 46. On-chip peripherals current consumption⁽¹⁾

Symbol	C	Parameter	Conditions		Typical value ⁽²⁾	Unit
$I_{DD_BV(CAN)}$	CC	CAN (FlexCAN) supply current on VDD_BV	Bitrate: 500 Kbyte/s	Total (static + dynamic) consumption:	$8 * f_{periph} + 85$	μA
			Bitrate: 125 Kbyte/s	<ul style="list-style-type: none"> FlexCAN in loop-back mode XTAL @ 8 MHz used as CAN engine clock source Message sending period is 580 μs 	$8 * f_{periph} + 27$	
$I_{DD_BV(eMIOS)}$	CC	eMIOS supply current on VDD_BV	Static consumption:		$29 * f_{periph}$	μA
			<ul style="list-style-type: none"> eMIOS channel OFF Global prescaler enabled 			
$I_{DD_BV(SPI)}$	CC	SPI (DSPI) supply current on VDD_BV	Dynamic consumption:		3	μA
			<ul style="list-style-type: none"> It does not change varying the frequency (0.003 mA) 			
$I_{DD_BV(SCI)}$	CC	SCI (LINFlex) supply current on VDD_BV	Total (static + dynamic) consumption:		$5 * f_{periph} + 31$	μA
			<ul style="list-style-type: none"> LIN mode Baudrate: 20 Kbyte/s 			
$I_{DD_BV(SPI)}$	CC	SPI (DSPI) supply current on VDD_BV	Ballast static consumption (only clocked)		1	μA
			Ballast dynamic consumption (continuous communication):		$16 * f_{periph}$	
			<ul style="list-style-type: none"> Baudrate: 2 Mbit/s Transmission every 8 μs Frame: 16 bits 			
$I_{DD_BV(ADC)}$	CC	ADC supply current on VDD_BV	$V_{DD} = 5.5 V$	Ballast static consumption (no conversion)	$41 * f_{periph}$	μA
				Ballast dynamic consumption (continuous conversion) ⁽³⁾	$5 * f_{periph}$	
$I_{DD_HV_ADC(ADC)}$	CC	ADC supply current on VDD_HV_ADC	$V_{DD} = 5.5 V$	Analog static consumption (no conversion)	$2 * f_{periph}$	μA
				Analog dynamic consumption (continuous conversion)	$75 * f_{periph} + 32$	
$I_{DD_HV(FLASH)}$	CC	Code Flash + Data Flash supply current on VDD_HV	$V_{DD} = 5.5 V$	—	8.21	mA
$I_{DD_HV(PLL)}$	CC	PLL supply current on VDD_HV	$V_{DD} = 5.5 V$	—	$30 * f_{periph}$	μA

1. Operating conditions: $T_A = 25^\circ C$, $f_{periph} = 8 \text{ MHz to } 64 \text{ MHz}$ 2. f_{periph} is an absolute value.

3. During the conversion, the total current consumption is given from the sum of the static and dynamic consumption, i.e.,
 $(41 + 5) \cdot f_{\text{periph}}$.

Table 50. LQFP64 mechanical data (continued)

Symbol	mm			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
D1	9.8	10	10.2	0.3858	0.3937	0.4016
D3	—	7.5	—	—	0.2953	—
E	11.8	12	12.2	0.4646	0.4724	0.4803
E1	9.8	10	10.2	0.3858	0.3937	0.4016
E3	—	7.5	—	—	0.2953	—
e	—	0.5	—	—	0.0197	—
L	0.45	0.6	0.75	0.0177	0.0236	0.0295
L1	—	1	—	—	0.0394	—
k	0.0°	3.5°	7.0°	0.0°	3.5°	7.0°
ccc	—	—	0.08	—	—	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Table 55. Document revision history (continued)

Date	Revision	Changes
06-Mar-2009	2 (continued)	<p>Updated tables:</p> <ul style="list-style-type: none"> – “I/O input DC electrical characteristics” – “I/O pull-up/pull-down DC electrical characteristics” – “SLOW configuration output buffer electrical characteristics” – “MEDIUM configuration output buffer electrical characteristics” – “FAST configuration output buffer electrical characteristics” <p>Added “Output pin transition times” section</p> <p>Updated “I/O consumption” table</p> <p>Updated “Start-up reset requirements” figure</p> <p>Updated “Reset electrical characteristics” table</p> <p>“Voltage regulator electrical characteristics” section:</p> <ul style="list-style-type: none"> – Amended description of LV_PLL <p>“Voltage regulator capacitance connection” figure:</p> <ul style="list-style-type: none"> – Exchanged position of symbols C_{DEC1} and C_{DEC2} <p>Updated tables”</p> <ul style="list-style-type: none"> – “Voltage regulator electrical characteristics” – “Low voltage monitor electrical characteristics” – “Low voltage power domain electrical characteristics” <p>Added “Low voltage monitor vs reset” figure</p> <p>Updated “Flash memory electrical characteristics” section</p> <p>Added “Electromagnetic compatibility (EMC) characteristics” section</p> <p>Updated “Fast external crystal oscillator (4 to 16 MHz) electrical characteristics” section</p> <p>Updated “Slow external crystal oscillator (32 kHz) electrical characteristics” section</p> <p>Updated tables:</p> <ul style="list-style-type: none"> – “FMPLL electrical characteristics” – “Fast internal RC oscillator (16 MHz) electrical characteristics” – “Slow internal RC oscillator (128 kHz) electrical characteristics” <p>Added “On-chip peripherals” section</p> <p>Added “ADC input leakage current” table</p> <p>Updated “ADC conversion characteristics” table</p> <p>Updated “ECOPACK®” section</p> <p>Corrected inverted column headings for typical and minimum dimensions in “LQFP64 mechanical data” and “LQFP100 mechanical data” tables</p> <p>Added “Abbreviation” appendix</p>
03-Jun-2009	3	Corrected “Commercial product code structure” figure